NSN 5961-01-294-4714

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-294-4714 **Inclosure Material:** Metal **Overall Length:** 1.645 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Burn in and hermetically sealed case **Overall Width Across Flats:** Between 0.551 inches and 0.559 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 repetitive peak reverse voltage, peak total value, gate terminal open-circuited and 75.0 nonrepetitive peak reverse voltage, peak total value, gate terminal open-circuited **Current Rating Per Characteristic:** 25.00 amperes source cutoff current preset and 200.00 amperes forward current, average preset **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector outside diameter and 0.5 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No